## Amendments to the Claims

Kindly amend the claims as follows:

- 1-7. Canceled.
- 8. (currently amended) A method of forming a patterned material structure on a substrate, said method comprising:
  - (A) providing a substrate with a layer of said material wherein said material is <a href="mailto:chromium-containing">chromium-containing</a> metal <a href="mailto:composition">composition</a>,
  - (B) applying a resist composition to said substrate to form a resist layer on said substrate, said resist composition comprising
    - a) an imaging polymer,
    - b) acid-labile moieties,
    - c) a radiation-sensitive acid generator, and
    - d) a base additive component, wherein said base additive component comprises:
      - (i) a room temperature solid base selected from the group consisting of aromatic amines and imidazoles, and
      - (ii) a liquid low vapor pressure base selected from the group consisting of triethanolamine, 1-naphthylamine, 2-naphthylamine, diphenylamine, acetanilide, 3,6,9-triazaundecamethylenediamine, 4,4'-propane-1,3-diylbismorpholine, and 1,8-azabicycloundecene,
  - (C) patternwise exposing said substrate to <u>electron beam radiation</u> whereby acid is generated by radiation-sensitive acid generator in exposed regions of said resist layer,

- (D) developing a patterned resist structure in said resist layer by removing radiation-exposed portions of said resist, and
- (E) transferring resist structure pattern to said material layer by removing portions of said material layer through spaces in said resist structure pattern.

## 9. Canceled.

- 10. (original) The method of claim 8 wherein said acid-labile protecting group is a moiety selected from the group consisting of ketals, acetals and orthoesters.
- 11. (original) The method of claim 8 wherein said transfer of step (F) comprises reactive ion etching.
- 12. (original) The method of claim 8 wherein at least one intermediate layer is provided between said material layer and said resist layer, and step (E) comprises etching through said intermediate layer.
- 13. (original) The method of claim 8 wherein said resist is thermally treated between steps (C) and (D).

14 - 19. Canceled.

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